

### Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

### Listing of Claims

1. (Currently Amended) A semiconductor device, comprising:  
a thin film transistor formed on ~~[[an]]~~ a first insulating surface of a substrate; ~~[[and]]~~  
a diamond-like carbon film formed on a ~~[[back]]~~ second insulating surface of the  
~~substrate, substrate;~~  
a wiring electrically connected to the thin film transistor; and  
a pixel electrode formed over the wiring,  
wherein the first insulating surface is opposite to the second insulating surface.
2. (Original) A semiconductor device according to claim 1, wherein the substrate is a quartz substrate.
3. (Original) A device according to claim 1, wherein the diamond-like carbon film has a specific resistance of  $10^7$  to  $10^{14}$   $\Omega\text{cm}$ .
4. (Original) A device according to claim 1, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.
5. (Original) A device according to claim 1, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.
6. (Currently Amended) A semiconductor device, comprising:  
a diamond-like carbon film formed on an insulating surface of a substrate;

an underlayer film formed on the diamond-like carbon film; ~~[[and]]~~  
a thin film transistor formed on the underlayer ~~[[film.]] film;~~  
a wiring electrically connected to the thin film transistor; and  
a pixel electrode formed over the wiring.

7. (Original) A device according to claim 6, wherein the substrate is a quartz substrate.

8. (Original) A device according to claim 6, wherein the diamond-like carbon film has a specific resistance of  $10^7$  to  $10^{14}$   $\Omega\text{cm}$ .

9. (Original) A device according to claim 6, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.

10. (Original) A device according to claim 6, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.

11. (Currently Amended) A semiconductor device, comprising:  
a thin film transistor formed over a substrate having an insulating surface;  
an interlayer insulating film formed over the thin film transistor and comprising a first opening;  
a diamond-like carbon film formed on the interlayer insulating film and comprising a second opening; and  
a pixel electrode formed over the diamond-like carbon ~~[[film.]] film,~~  
wherein the pixel electrode is electrically connected to the thin film transistor through the first opening and the second opening.

12-13. (Canceled)

14. (Original) A device according to claim 11, wherein the diamond-like carbon film has a specific resistance of  $10^7$  to  $10^{14}$   $\Omega\text{cm}$ .

15. (Original) A device according to claim 11, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.

16. (Original) A device according to claim 11, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.

17-32. (Canceled)

33. (Currently Amended) An electronic device comprising:  
a thin film transistor formed ~~[[over]]~~ on a first insulating surface of a substrate; ~~[[and]]~~  
a diamond-like carbon film formed ~~[[over]]~~ on a second insulating surface of the  
~~substrate; substrate;~~  
a wiring electrically connected to the thin film transistor; and  
a pixel electrode formed over the wiring,  
wherein the first insulating surface is opposite to the second insulating surface.

34. (Previously Presented) A device according to claim 33, wherein the substrate is a quartz substrate.

35. (Previously Presented) A device according to claim 33, wherein the diamond-like carbon film has a specific resistance of  $10^7$  to  $10^{14}$   $\Omega\text{cm}$ .

36. (Previously Presented) A device according to claim 33, wherein said electronic device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus comprising a recording medium, a digital camera, a front type projector, and a rear type projector.

37. (Currently Amended) An electronic device comprising:  
a diamond-like carbon film formed ~~[[over]]~~ on an insulating surface of the substrate;  
an underlayer film formed on the diamond-like carbon film; and  
a thin film transistor formed on the underlayer film; ~~film~~;  
a wiring electrically connected to the thin film transistor; and  
a pixel electrode formed over the wiring.

38. (Previously Presented) A device according to claim 37, wherein the substrate is a quartz substrate.

39. (Previously Presented) A device according to claim 37, wherein the diamond-like carbon film has a specific resistance of  $10^7$  to  $10^{14}$   $\Omega\text{cm}$ .

40. (Previously Presented) A device according to claim 37, wherein said electronic device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus comprising a recording medium, a digital camera, a front type projector, and a rear type projector.

41-48. (Canceled)

49. (Previously Presented) A device according claim 1, further comprising a buffer layer having at least one of silicon, silicon carbide, and silicon nitride.

50. (Previously Presented) A device according claim 6, further comprising a buffer layer having at least one of silicon, silicon carbide, and silicon nitride.

51-54. (Canceled)

55. (Previously Presented) A device according claim 1, further comprising a buffer layer having a thickness of 80 to 200 nm.

56. (Previously Presented) A device according claim 6, further comprising a buffer layer having a thickness of 80 to 200 nm.

57-60. (Canceled)

61. (Currently Amended) A semiconductor device, comprising:  
a diamond-like carbon film;  
a substrate over the diamond like carbon film; and  
a logic circuit comprising a transistor formed over the substrate.

62. (Previously Presented) A semiconductor device according to claim 61, wherein the substrate is a quartz substrate.

63. (Previously Presented) A device according to claim 61, wherein the diamond-like carbon film has a specific resistance of  $10^7$  to  $10^{14}$   $\Omega\text{cm}$ .

64. (Previously Presented) A device according to claim 61, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.

65. (Previously Presented) A device according to claim 61, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.

66. (New) A semiconductor device according to claim 61, wherein the logic circuit is a signal processing circuit.

67. (New) A semiconductor device according to claim 66, wherein the signal processing circuit comprises at least one selected from the group consisting of an A/D converter circuit, a  $\gamma$ -correction circuit, and a memory circuit.

68. (New) A semiconductor device according to claim 61, wherein the logic circuit is a computation processing circuit.

69. (New) A semiconductor device comprising:  
a diamond-like carbon film formed on an insulating surface of a substrate; and  
a logic circuit comprising a thin film transistor formed over the diamond-like carbon film.

70. (New) A semiconductor device according to claim 69, wherein the substrate is a quartz substrate.

71. (New) A device according to claim 69, wherein the diamond-like carbon film has a specific resistance of  $10^7$  to  $10^{14}$   $\Omega\text{cm}$ .

72. (New) A device according to claim 69, wherein said semiconductor device is an active matrix type display device having a pixel region and a driver region on the substrate.

73. (New) A device according to claim 69, wherein said semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggles-type display, a player apparatus having a recording medium, a digital camera, a front type projector, and a rear type projector.

74. (New) A semiconductor device according to claim 69, wherein the logic circuit is a signal processing circuit.

75. (New) A semiconductor device according to claim 74, wherein the signal processing circuit comprises at least one selected from the group consisting of an A/D converter circuit, a  $\gamma$ -correction circuit, and a memory circuit.

76. (New) A semiconductor device according to claim 69, wherein the logic circuit is a computation processing circuit.